## INTEGRATED CIRCUITS

## DATA SHEET

# **UBA2030T**Full bridge driver IC

Product specification Supersedes data of 1999 Aug 10 2002 Sep 27





## Full bridge driver IC

#### **UBA2030T**

#### **FEATURES**

- · Full bridge driver
- · Integrated bootstrap diodes
- · Integrated high voltage level shift function
- High voltage input (570 V maximum) for the internal supply
- · Adjustable 'dead time'
- · Adjustable oscillator frequency
- High voltage level shifter for the bridge enable function
- Shut-down function.

#### **APPLICATIONS**

- The UBA2030T can drive the MOSFETs in any type of load configured as a full bridge
- The circuit is intended as a commutator for High Intensity Discharge (HID) lamps.

#### **GENERAL DESCRIPTION**

The UBA2030T is a high voltage integrated circuit fabricated using the BCD750 power logic process. The circuit is designed for driving the MOSFETs in a full bridge configuration. In addition, it features a shut-down function, an adjustable oscillator and a PMOS high voltage level shifter to control the bridge enable function. To guarantee an accurate 50% duty factor, the oscillator signal passes through a divider before being fed to the output drivers.

#### **ORDERING INFORMATION**

| TYPE NUMBER  |      | PACKAGE   |  |  |  |
|--------------|------|---|--|--|--|
| TIPE NOWIBER | NAME | NAME DESCRIPTION VERSION                                      |  |  |  |
| UBA2030T     | SO24 | plastic small outline package; 24 leads; body width 7.5 mm SC |  |  |  |

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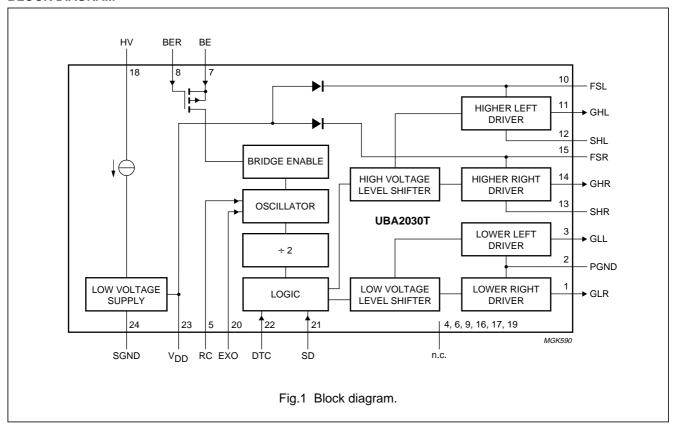
#### QUICK REFERENCE DATA

| SYMBOL                                   | PARAMETER                           | CONDITIONS   | MIN. | TYP. | MAX.            | UNIT |
|--|-------------------------------------|--|------|------|-----------------|------|
| High volta                               | ige                                 |  | •    |      | '               |      |
| V <sub>HV</sub>                          | high voltage supply                 |  | 0    | _    | 570             | V    |
| Start-up;                                | powered via pin HV                  |  | •    |      | •               |      |
| I <sub>strtu</sub>                       | start-up current                    |  | _    | 0.7  | 1.0             | mA   |
| $V_{th(oscstrt)}$                        | start oscillating threshold voltage | at f <sub>bridge</sub> = 500 Hz; no load   | 14.0 | 15.5 | 17.0            | V    |
| V <sub>th(oscstp)</sub>                  | stop oscillating threshold voltage  |  | 11.5 | 13.0 | 14.5            | V    |
| Output dr                                | ivers                               |  | •    | •    | •               |      |
| I <sub>o(source)</sub>                   | output source current               | $V_{DD} = V_{FSL} = V_{FSR} = 15 \text{ V};$<br>$V_{GHR} = V_{GHL} = V_{GLR} = V_{GLL} = 0 \text{ V}$  | 140  | 190  | 240             | mA   |
| I <sub>o(sink)</sub>                     | output sink current                 | $V_{DD} = V_{FSL} = V_{FSR} = 15 \text{ V};$<br>$V_{GHR} = V_{GHL} = V_{GLR} = V_{GLL} = 15 \text{ V}$ | 200  | 260  | 320             | mA   |
| Internal o                               | scillator                           |  |      |      |                 |      |
| f <sub>bridge</sub>                      | bridge oscillating frequency        | EXO pin connected to SGND  | 50   | _    | 50000           | Hz   |
| External c                               | escillator                          |  |      |      |                 |      |
| f <sub>osc(ext)</sub>                    | external oscillator frequency       | RC pin connected to SGND; $f_{bridge} = \frac{f_{osc(ext)}}{2}$  | 100  | _    | 100000          | Hz   |
| Dead time                                | control                             |  |      |      |                 |      |
| t <sub>dead</sub>                        | dead time control range             | adjusted externally  | 0.4  | _    | 4               | μs   |
| Bridge en                                | able                                |  |      |      | •               |      |
| I <sub>IH</sub>                          | HIGH-level input current            | bridge enable active   | 100  | _    | 700             | μА   |
| I <sub>IL</sub>                          | LOW-level input current             | bridge enable not active   | 0    | _    | 20              | μΑ   |
| Shut-dow                                 | n                                   |  |      |      |                 |      |
| V <sub>IH</sub> HIGH-level input voltage |                                     | shut-down active; $\left  \frac{\Delta V_{SD}}{\Delta t} \right  > 5 \text{ V/ms}$                     | 4.5  | _    | V <sub>DD</sub> | V    |
| V <sub>IL</sub>                          | LOW-level input voltage             | shut-down not active; $\left  \frac{\Delta V_{SD}}{\Delta t} \right  > 5 \text{ V/ms}$                 | 0    | _    | 0.5             | V    |

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#### **BLOCK DIAGRAM**

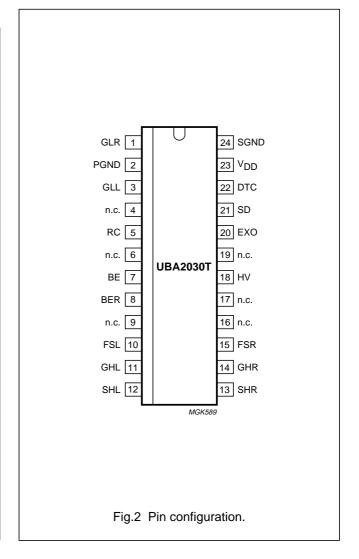


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#### **PINNING**

| 0)/145.01       |     | DECODIDETION                       |
|-----------------|-----|------------------------------------|
| SYMBOL          | PIN | DESCRIPTION                        |
| GLR             | 1   | gate of lower right MOSFET         |
| PGND            | 2   | power ground for sources of lower  |
|                 |     | left and right MOSFETs             |
| GLL             | 3   | gate of lower left MOSFET          |
| n.c.            | 4   | not connected                      |
| RC              | 5   | RC input for internal oscillator   |
| n.c.            | 6   | not connected                      |
| BE              | 7   | bridge enable control input        |
| BER             | 8   | bridge enable reference input      |
| n.c.            | 9   | not connected                      |
| FSL             | 10  | floating supply voltage left side  |
| GHL             | 11  | gate of higher left MOSFET         |
| SHL             | 12  | source of higher left MOSFET       |
| SHR             | 13  | source of higher right MOSFET      |
| GHR             | 14  | gate of higher right MOSFET        |
| FSR             | 15  | floating supply voltage right side |
| n.c.            | 16  | not connected                      |
| n.c.            | 17  | not connected                      |
| HV              | 18  | high voltage supply                |
| n.c.            | 19  | not connected                      |
| EXO             | 20  | external oscillator input          |
| SD              | 21  | shut-down input                    |
| DTC             | 22  | 'dead time' control input          |
| V <sub>DD</sub> | 23  | internal (low voltage) supply      |
| SGND            | 24  | signal ground                      |



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#### **FUNCTIONAL DESCRIPTION**

#### Supply voltage

The UBA2030T is powered by a single supply voltage connected to the HV pin (the full bridge supply could be used, for example). The IC generates its own low voltage supply for driving the internal circuitry and the MOSFETs in the full bridge, removing the need for an additional low voltage supply. A capacitor must be connected between the  $V_{\rm DD}$  pin and SGND to obtain a ripple-free internal supply voltage.

#### Start-up

When the power is turned on, the UBA2030T enters a start-up phase; the high side MOSFETs are switched off and the low side MOSFETs switched on. During start-up, the bootstrap capacitors are charged and the bridge output current is zero.

#### Oscillation

At the point where the supply voltage at the HV pin crosses the 'start oscillating threshold', the bridge begins commutating between the following two defined states:

- Higher left and lower right MOSFETs on and higher right and lower left MOSFETs off
- Higher left and lower right MOSFETs off and higher right and lower left MOSFETs on.

When the internal oscillator is used, the bridge commutating frequency is determined by the values of an external resistor and capacitor. In this mode, the EXO pin must be connected to SGND.

When an external oscillator is used, its output must be connected to the EXO pin; the internal oscillator must be disabled by connecting the RC pin to SGND. The bridge commutating frequency is half the oscillator frequency due to a ÷2 circuit which guarantees an accurate 50% duty factor.

The time between turning off the conducting pair of MOSFETs and turning on the other pair, the 'dead time', can be adjusted using an external resistor. If the supply voltage at the HV pin falls below the 'stop oscillating threshold', the UBA2030T re-enters the start-up phase.

#### Bridge enable

The bridge enable function allows the bridge to be held in its current state. When active, it connects the RC pin to SGND, disabling the internal oscillator. If the bridge enable function is activated during 'dead time', the bridge is allowed to enter the next conducting state before being held. Oscillations resume the instant the bridge enable function is turned off. A timing diagram is shown in Fig.3.

To hold the bridge, an external control circuit is required to provide a source current to the bridge enable control input (pin BE), and to supply a reference voltage to pin BER (see Fig.6).

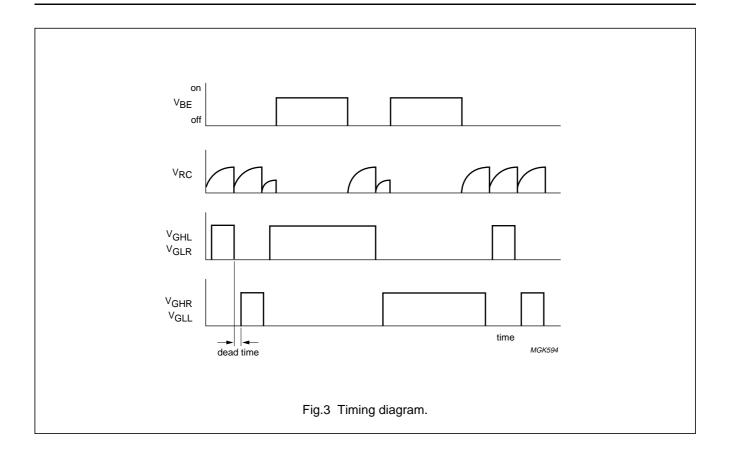
#### Shut-down

The active HIGH shut-down input (pin SD) can be used at any time to turn off all four MOSFETs. However, if the supply voltage drops below the 'stop oscillating threshold', the bridge re-enters the start-up phase even if the shut-down function is active.

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL                              | PARAMETER   | CONDITIONS  | MIN.      | MAX.            | UNIT |
|-------------------------------------|---|---|-----------|-----------------|------|
| $V_{DD}$                            | supply voltage (low voltage)                      |   | 0         | 18              | V    |
| V <sub>HV</sub>                     | supply voltage (high voltage)                     | note 1  | 0         | 570             | V    |
| V <sub>FSL</sub> , V <sub>FSR</sub> | floating supply voltage                           | V <sub>SHL</sub> = V <sub>SHR</sub> = 570 V, note 1 | 570       | 588             | V    |
|                                     |   | V <sub>SHL</sub> = V <sub>SHR</sub> = 0 V           | 0         | 18              | V    |
| V <sub>SHL</sub> , V <sub>SHR</sub> | source voltage for higher right and left MOSFETs  | with reference to PGND and SGND                     | -10       | +570            | V    |
| $V_{PGND}$                          | power ground voltage                              | with reference to SGND                              | <b>-7</b> | +10             | V    |
| V <sub>i(BER)</sub>                 | bridge enable reference input voltage             |   | 0         | 570             | V    |
| V <sub>i(BE)</sub>                  | bridge enable control input voltage               | V <sub>i(BER)</sub> = 570 V                         | 570       | 580             | V    |
|                                     |   | $V_{i(BER)} = 0 V$                                  | 0         | 10              | V    |
| I <sub>i(BE)</sub>                  | bridge enable control input current               |   | 0         | 700             | μΑ   |
| V <sub>i(EXO)</sub>                 | input voltage from external oscillator on pin EXO |   | 0         | V <sub>DD</sub> | V    |
| V <sub>i(SD)</sub>                  | shut-down input voltage on pin SD                 |   | 0         | $V_{DD}$        | V    |
| SR                                  | slew rate at output pins                          | repetitive  | -4        | +4              | V/ns |
| Tj                                  | junction temperature                              |   | -40       | +150            | °C   |
| T <sub>amb</sub>                    | ambient temperature                               |   | -40       | +150            | °C   |
| T <sub>stg</sub>                    | storage temperature                               |   | -55       | +150            | °C   |
| V <sub>esd</sub>                    | electrostatic discharge voltage                   | note 2  |           |                 |      |
|                                     | pin HV  |   | -1250     | +1250           | V    |
|                                     | pins BE, BER, FSL, GHL, SHL,<br>SHR, GHR and FSR  |   | -1500     | +1500           | V    |

#### Notes

- 1. This value is guaranteed down to  $T_j = -25$  °C. From  $T_j = -25$  to -40 °C, the voltage on pin HV is limited to 530 V and the floating supply voltage (V<sub>FSL</sub>, V<sub>FSR</sub>) is limited to a maximum value of 548 V.
- 2. In accordance with the human body model: equivalent to discharging a 100 pF capacitor through a 1.5 k $\Omega$  series resistor.

#### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                   | VALUE | UNIT |
|----------------------|---|-------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | 70    | K/W  |

#### **QUALITY SPECIFICATION**

In accordance with "General Quality Specifications for Integrated Circuits SNW-FQ-611D".

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#### **CHARACTERISTICS**

 $T_j$  = 25 °C; all voltages with respect to PGND; positive currents flow into the IC.

| SYMBOL   | PARAMETER   | CONDITIONS  | MIN. | TYP. | MAX. | UNIT |
|--|---|---|------|------|------|------|
| High voltag  | e   |   | •    | -1   | 1    | !    |
| V <sub>HV</sub>  | high voltage supply   |   | 0    | _    | 570  | V    |
| IL   | leakage current   | with 570 V applied to pins BER, SHR and SHL                                   | _    | _    | 5    | μΑ   |
| V <sub>PGND(float)</sub> ,<br>V <sub>SGND(float)</sub> | floating ground voltage   |   | 0    | _    | 5    | V    |
| Start-up, po   | owered via the HV pin; note 1   |   |      | •    | •    | •    |
| I <sub>strtu</sub>                                     | start-up current  |   | _    | 0.7  | 1.0  | mA   |
| V <sub>strtu</sub>                                     | start-up voltage  | high left and right MOSFETs off; low left and right MOSFETs on                | _    | 6    | -    | V    |
| V <sub>th(oscstrt)</sub>                               | start oscillating threshold voltage   | f <sub>bridge</sub> = 500 Hz; no load   | 14.0 | 15.5 | 17.0 | V    |
| V <sub>th(oscstp)</sub>                                | stop oscillating threshold voltage  |   | 11.5 | 13.0 | 14.5 | V    |
| V <sub>hys</sub>                                       | hysteresis voltage  | between oscillation start and stop levels                                     | 2.0  | 2.5  | 3.0  | V    |
| I <sub>HV</sub>  | supply current  | $f_{bridge} = 500 \text{ Hz}$ ; no load; $V_{HV} = 50 \text{ V}$              | 0.3  | 0.5  | 0.7  | mA   |
| $V_{DD}$   | internal supply voltage (low  | $f_{bridge} = 500 \text{ Hz}$ ; no load; $V_{HV} = 50 \text{ V}$              | 14.0 | 15.3 | 16.5 | V    |
|  | voltage)  | f <sub>bridge</sub> = 500 Hz; no load; at start oscillating threshold         | 10.5 | 11   | 11.5 | V    |
|  |   | f <sub>bridge</sub> = 500 Hz; no load; at stop oscillating threshold          | 8.0  | 8.5  | 9.0  | V    |
| Output driv  | ers   |   |      | ,    | •    |      |
| $V_{o(GHL)},$ $V_{o(GHR)}$                             | output voltage on pins GHL<br>and GHR for gates of higher<br>right and left MOSFETs | at power-up; no load; $V_{HV} = 50 \text{ V}$ ; $f_{bridge} = 500 \text{ Hz}$ | 13.2 | 14.5 | 16.5 | V    |
| $V_{o(GLL)},$ $V_{o(GLR)}$                             | output voltage on pins GLL<br>and GLR for gates of lower<br>right and left MOSFETs  |   | 14.0 | 15.3 | 16.5 | V    |
| Δt   | time difference between diagonally placed output drivers                            |   | 0    | _    | 100  | ns   |
| R <sub>on(HL)</sub> ,<br>R <sub>on(HR)</sub>           | higher MOSFETs on resistance  | $V_{FSR} = V_{FSL} = 15 \text{ V}; I_{source} = 50 \text{ mA}$                | 33   | 39   | 46   | Ω    |
| R <sub>off(HL)</sub> ,<br>R <sub>off(HR)</sub>         | higher MOSFETs off resistance   | $V_{FSR} = V_{FSL} = 15 \text{ V}; I_{sink} = 50 \text{ mA}$                  | 11   | 14   | 17   | Ω    |
| R <sub>on(LL)</sub> ,<br>R <sub>on(LR)</sub>           | lower MOSFETs on resistance   | V <sub>DD</sub> = 15 V; I <sub>source</sub> = 50 mA                           | 33   | 39   | 46   | Ω    |
| R <sub>off(LL)</sub> ,<br>R <sub>off(LR)</sub>         | lower MOSFETs off resistance  | V <sub>DD</sub> = 15 V; I <sub>sink</sub> = 50 mA                             | 11   | 14   | 17   | Ω    |
| V <sub>diode</sub>                                     | bootstrap diode voltage drop  | I <sub>diode</sub> = 1 mA   | 0.8  | 1.0  | 1.2  | V    |

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| SYMBOL   | PARAMETER   | CONDITIONS   | MIN. | TYP. | MAX.            | UNIT  |
|--|---|--|------|------|-----------------|-------|
| I <sub>o(source)</sub>                               | output source current   | $V_{DD} = V_{FSL} = V_{FSR} = 15 \text{ V};$<br>$V_{GHR} = V_{GHL} = V_{GLR} = V_{GLL} = 0 \text{ V}$  | 140  | 190  | 240             | mA    |
| I <sub>o(sink)</sub>                                 | output sink current   | $V_{DD} = V_{FSL} = V_{FSR} = 15 \text{ V};$<br>$V_{GHR} = V_{GHL} = V_{GLR} = V_{GLL} = 15 \text{ V}$ | 200  | 260  | 320             | mA    |
| I <sub>FSL(float)</sub> ,<br>I <sub>FSR(float)</sub> | floating supply current   | V <sub>FSL</sub> = V <sub>FSR</sub> = 15 V   | _    | 15   | _               | μΑ    |
| Internal osc   | illator; notes 2 and 3  |  |      | •    | •               |       |
| f <sub>bridge</sub>                                  | bridge oscillating frequency  | EXO pin connected to SGND  | 50   | _    | 50000           | Hz    |
| $\Delta f_{\rm osc}/\Delta T$                        | oscillator frequency<br>dependency with respect to<br>temperature     | fixed RC; $\Delta T = -40$ °C to +150 °C   | 0    | -    | 10              | %     |
| $\Delta f_{osc}/\Delta V_{DD}$                       | oscillator frequency<br>dependency with respect to<br>V <sub>DD</sub> | fixed RC; $\Delta V_{DD} = 12$ to 16 V   | 0    | -    | 10              | %     |
| k <sub>H</sub>                                       | HIGH-level trip point   | $V_{RCH} = k_H \times V_{DD}$  | 0.67 | 0.71 | 0.75            |       |
| k <sub>L</sub>                                       | LOW-level trip point  | $V_{RCL} = k_L \times V_{DD}$  | _    | 0.01 | _               |       |
| k <sub>osc</sub> oscillator constant                 |   | $f_{bridge} = \frac{1}{k_{osc} \times R_{osc} \times C_{osc}}$   | 2.34 | 2.49 | 2.64            |       |
| External os  | cillator; note 2  |  | •    | •    | •               | •     |
| f <sub>osc(ext)</sub>                                | external oscillator frequency   | RC pin connected to SGND; $f_{bridge} = \frac{f_{osc(ext)}}{2}$  | 100  | _    | 100000          | Hz    |
| V <sub>IH</sub>                                      | HIGH-level input voltage  | $\left  \frac{\Delta V_{EXO}}{\Delta t} \right  > 5 \text{ V/ms}$                                      | 4.5  | -    | V <sub>DD</sub> | V     |
| V <sub>IL</sub>                                      | LOW-level input voltage   | $\left  \frac{\Delta V_{EXO}}{\Delta t} \right  > 5 \text{ V/ms}$                                      | 0    | -    | 0.5             | V     |
| I <sub>i(EXO)</sub>                                  | input current   |  | 0    | _    | 50              | μΑ    |
| Dead time c  | control; notes 2 and 4  |  | •    | •    | •               |       |
| t <sub>dead</sub>                                    | dead time control range   | adjusted externally  | 0.4  | _    | 4               | μs    |
| k <sub>DT</sub>                                      | dead time variable  |  | 180  | 270  | 380             | kΩ/μs |
|  | ole; notes 2 and 5  |  | -    |      | 1               |       |
| I <sub>IH</sub>                                      | HIGH-level input current  | bridge enable active   | 100  | Ī-   | 700             | μΑ    |
| •  |   | note 6   | 1-   | 1.1  | 1-              | mA    |
| I <sub>IL</sub>                                      | LOW-level input current   | bridge enable not active   | 0    | 1-   | 20              | μΑ    |
| V <sub>BE</sub> – V <sub>BER</sub>                   | threshold voltage:  | I <sub>IH</sub> = 100 μA   |      |      |                 |       |
|  | with reference to HV  |  | 2.1  | 2.6  | 3.0             | V     |
|  | with reference to PGND  |  | 3.5  | 5.5  | 7.5             | V     |

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| SYMBOL             | PARAMETER                | CONDITIONS   | MIN. | TYP. | MAX.            | UNIT |
|--------------------|--------------------------|--|------|------|-----------------|------|
| Shut-down;         | note 2                   |  | •    |      | •               |      |
| V <sub>IH</sub>    | HIGH-level input voltage | shut-down active; $\left  \frac{\Delta V_{SD}}{\Delta t} \right  > 5 \text{ V/ms}$   | 4.5  | _    | V <sub>DD</sub> | V    |
| V <sub>IL</sub>    | LOW-level input voltage  | shut-down not active; $\left \frac{\Delta V_{SD}}{\Delta t}\right  > 5 \text{ V/ms}$ | 0    | _    | 0.5             | V    |
| I <sub>i(SD)</sub> | input current            |  | 0    | _    | 50              | μΑ   |

#### **Notes**

- 1. The current into pin HV is internally limited to 15 mA at  $T_i$  = 25 °C and to 10 mA at  $T_i$  = 150 °C.
- 2.  $V_{DD} = 15 \text{ V}$ .
- 3. The internal ÷2 circuit requires the frequency of the internal or external oscillator to be twice the bridge frequency. When the internal oscillator is used, the bridge frequency can be adjusted using an external resistor and capacitor:

$$f_{bridge} = \frac{1}{2.8 \times R_{osc} \times C_{osc}}$$

where  $R_{osc(min)}$  = 200 k $\Omega$  and  $R_{osc(max)}$  = 2 M $\Omega$  with low leakage current.

- 4. The 'dead time' is adjusted using an external resistor ( $R_{DT}$ ) connected between pins DTC and SGND. The value is calculated as:  $R_{DT}$  = 270 x  $t_{dead}$  70, where the units are  $k\Omega$  for  $R_{DT}$  and  $\mu s$  for  $t_{dead}$ . The minimum value  $R_{DT(min)}$  = 50  $k\Omega$  and the maximum value  $R_{DT(max)}$  = 1  $M\Omega$ .
- 5. This function is disabled when using an external oscillator.
- 6.  $I_{IH}$  < 2.1 mA when the condition is  $V_{BE}$   $V_{BER}$  = 5 V at  $T_i$  = 150 °C.

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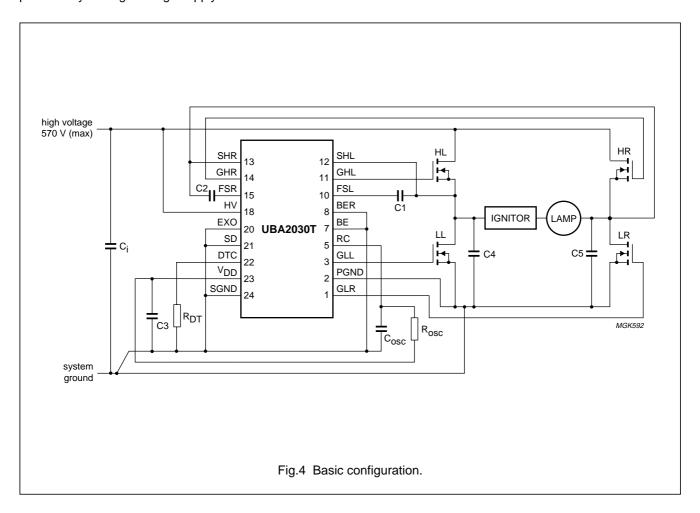
**UBA2030T** 

#### **APPLICATION INFORMATION**

#### **Basic application**

A basic full bridge configuration with an HID lamp is shown in Fig.4. The bridge enable and shut-down functions are not used in this application. The EXO, BE, BER and SD pins are connected to system ground. The IC is powered by the high voltage supply.

When the internal oscillator is used, the bridge commutating frequency is determined by the values of  $R_{\rm osc}$  and  $C_{\rm osc}.$  The bridge starts oscillating when the HV supply voltage exceeds the 'start oscillating threshold' (typically 15.5 V). If the supply voltage at the HV pin falls below the 'stop oscillating threshold' (typically 13 V), the UBA2030T enters the start-up state.



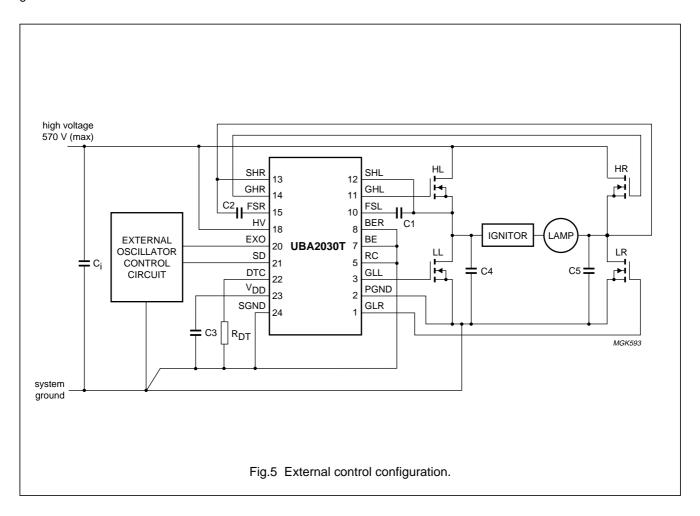
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#### Application with external control

Figure 5 shows an application containing an external oscillator control circuit referenced to system ground. The RC, BER and BE pins are connected to system ground.

The bridge commutation frequency is determined by the external oscillator. The shut-down input (pin SD) can be used to quickly turn off all four MOSFETs in the full bridg



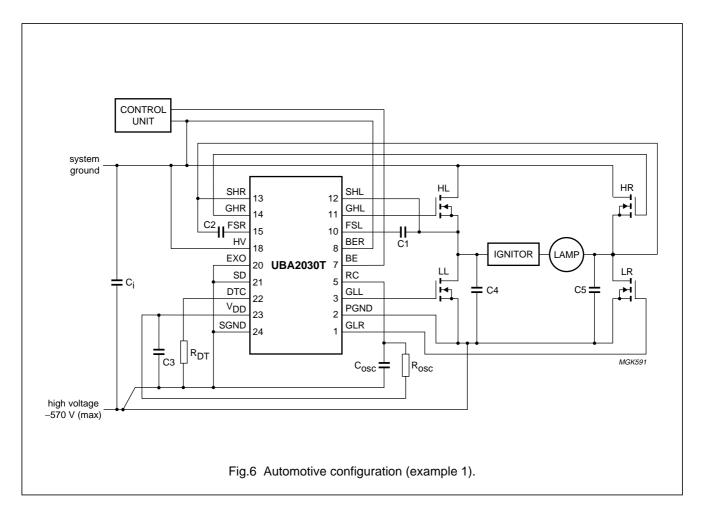
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#### **Automotive application**

The life of an HID lamp depends on the rate of sodium migration through its quartz wall. To minimize this, the lamp must be operated negative with respect to system ground.

Figure 6 shows a full bridge with an HID lamp in an automotive environment, and a control circuit referenced to the high side of the bridge. The BER and HV pins are connected to system ground. The bridge can be held in its current state using the BE pin. See the timing diagram in Fig.3.



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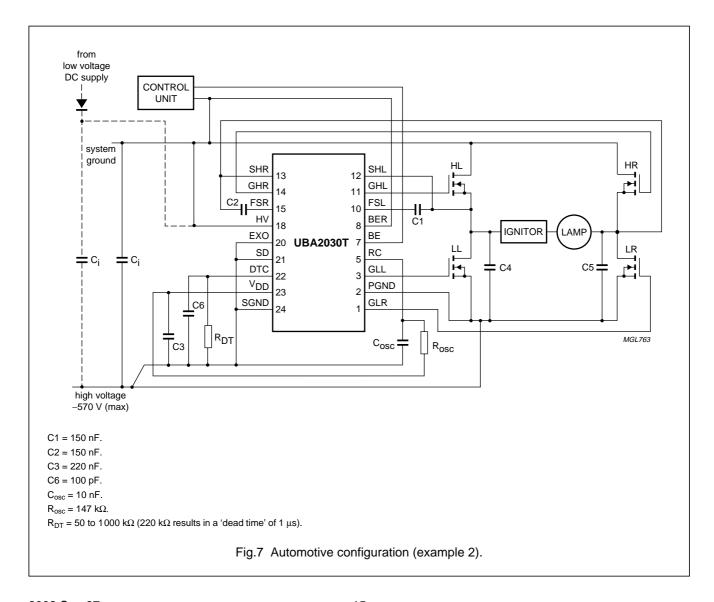
#### Additional application information

The UBA2030T is the commutator part in a complete system for driving an HID lamp. The life of the HID lamp can depend on the amount of sodium that migrates through its quartz wall. To minimize this migration, the lamp must be operated negative with respect to system ground.

Figure 7 shows a full bridge with an HID lamp in a typical automotive configuration using a control unit referenced to the high side of the bridge. Pin BER is connected to system ground. The bridge can be held in its current state by pin BE. The supply current to the internal low voltage circuit is fed to pin HV which can be connected to either system ground or to a low voltage DC supply, such as a battery, as indicated by the dotted lines in Fig.7.

The diode in series with the supply to pin HV prevents  $C_i$  being discharged if the lamp is shorted during the ignition phase. C6 should be positioned as close as possible to pin DTC. The control unit drives the MOSFETs relatively hard which can cause radiation. To prevent switching the MOSFETs hard, a resistor can be connected in series with each gate.

In all applications, the voltage on pin HV must not be allowed to become lower than the voltage at pin  $V_{DD}$  during the start-up phase or during normal operation, otherwise the full bridge will not operate correctly. During the start-up phase, pin EXO and pin SD should both be LOW. The voltage as a function of time at pin EXO and pin SD should be >5 V/ms.



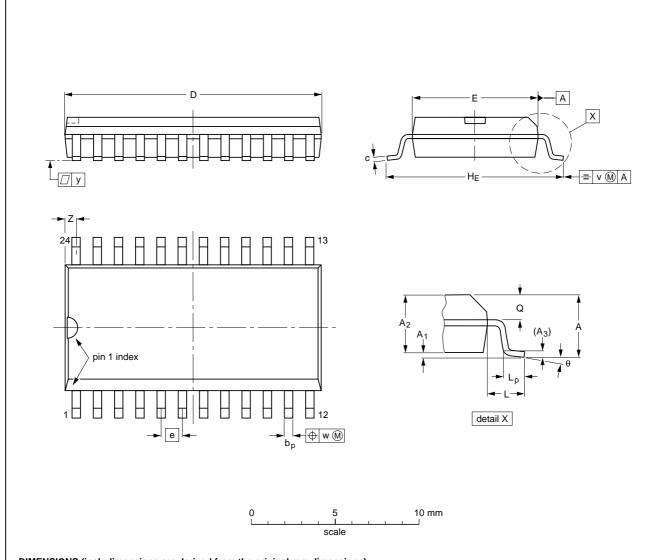
## Full bridge driver IC

**UBA2030T** 

#### **PACKAGE OUTLINE**

SO24: plastic small outline package; 24 leads; body width 7.5 mm

SOT137-1



#### **DIMENSIONS** (inch dimensions are derived from the original mm dimensions)

| UNIT   | A<br>max. | A <sub>1</sub> | A <sub>2</sub> | A <sub>3</sub> | bp             | С              | D <sup>(1)</sup> | E <sup>(1)</sup> | е     | HE             | L     | Lp             | Q          | ٧    | w    | у     | z <sup>(1)</sup> | θ  |
|--------|-----------|----------------|----------------|----------------|----------------|----------------|------------------|------------------|-------|----------------|-------|----------------|------------|------|------|-------|------------------|----|
| mm     | 2.65      | 0.30<br>0.10   | 2.45<br>2.25   | 0.25           | 0.49<br>0.36   | 0.32<br>0.23   | 15.6<br>15.2     | 7.6<br>7.4       | 1.27  | 10.65<br>10.00 | 1.4   | 1.1<br>0.4     | 1.1<br>1.0 | 0.25 | 0.25 | 0.1   | 0.9<br>0.4       | 8° |
| inches | 0.10      | 0.012<br>0.004 | 0.096<br>0.089 | 0.01           | 0.019<br>0.014 | 0.013<br>0.009 | 0.61<br>0.60     | 0.30<br>0.29     | 0.050 | 0.419<br>0.394 | 0.055 | 0.043<br>0.016 |            | 0.01 | 0.01 | 0.004 | 0.035<br>0.016   | 0° |

#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

| OUTLINE  |             | EUROPEAN | ISSUE DATE |  |            |                                 |
|----------|-------------|----------|------------|--|------------|---------------------------------|
| VERSION  | VERSION IEC |          | EIAJ       |  | PROJECTION | ISSUE DATE                      |
| SOT137-1 | 075E05      | MS-013   |            |  |            | <del>97-05-22</del><br>99-12-27 |

#### Full bridge driver IC

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#### **SOLDERING**

#### Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

#### Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

#### Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320  $^{\circ}$ C.

#### Full bridge driver IC

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#### Suitability of surface mount IC packages for wave and reflow soldering methods

| PACKAGE <sup>(1)</sup>   | SOLDERING METHOD                  |                       |  |  |
|--|-----------------------------------|-----------------------|--|--|
| PACKAGE  | WAVE                              | REFLOW <sup>(2)</sup> |  |  |
| BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA                             | not suitable                      | suitable              |  |  |
| HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS | not suitable <sup>(3)</sup>       | suitable              |  |  |
| PLCC <sup>(4)</sup> , SO, SOJ                                    | suitable                          | suitable              |  |  |
| LQFP, QFP, TQFP  | not recommended <sup>(4)(5)</sup> | suitable              |  |  |
| SSOP, TSSOP, VSO   | not recommended <sup>(6)</sup>    | suitable              |  |  |

#### **Notes**

- 1. For more detailed information on the BGA packages refer to the "(LF)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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#### **DATA SHEET STATUS**

| DATA SHEET STATUS(1) | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITIONS  |
|----------------------|----------------------------------|--|
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